

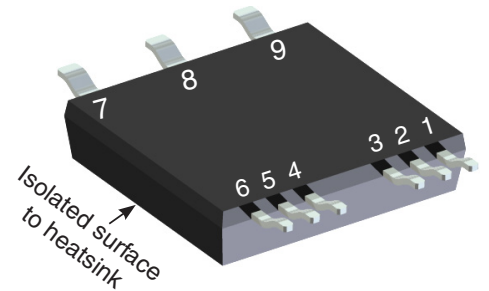
SiC Power MOSFET


$$I_{D25} = 38 \text{ A}$$

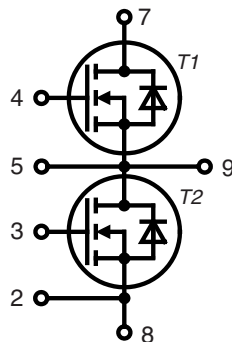
$$V_{DSS} = 1200 \text{ V}$$

$$R_{DS(on) \text{ max}} = 52 \text{ m}\Omega$$

Part number
 MCB30P1200LB



 E72873



Features / Advantages:

- High speed switching with low capacitances
- High blocking voltage with low $R_{DS(on)}$
- Easy to parallel and simple to drive
- Resistant to latch-up
- Real Kelvin source connection

Applications:

- Solar inverters
- High voltage DC/DC converters
- Motor drives
- Switch mode power supplies
- UPS
- Battery chargers
- Induction heating

Package: SMPD

- DCB isolated backside
- Isolation Voltage 2500 V
- Epoxy meets UL 94V-0
- RoHS compliant
- Advanced power cycling

Disclaimer Notice

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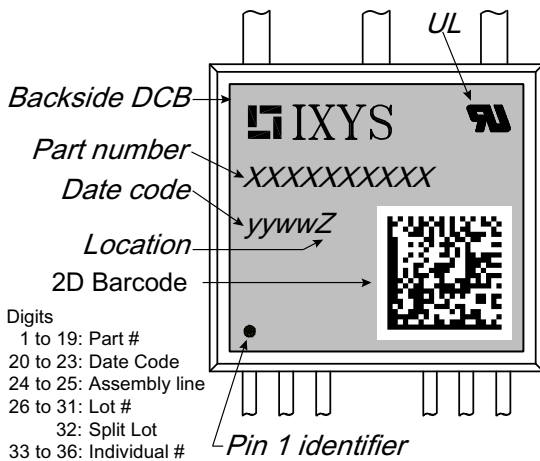
MOSFET				Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.		
$V_{(BR)DSS}$	drain source breakdown voltage	$I_D = 100 \mu A$	1200			V	
$V_{GS(max)}$	max transient gate source voltage		-10		+25	V	
V_{GS}	continous gate source voltage	recommended operational value	-5		+20	V	
I_{D25}	drain current	$V_{GS} = 20 V$			38	A	
I_{D80}			$T_C = 25^\circ C$			30	A
I_{D100}			$T_C = 80^\circ C$			27	A
$R_{DS(on)}$	static drain source on resistance	$I_D = 40 A; V_{GS} = 20 V$			40	mΩ	
					90	mΩ	
$V_{GS(th)}$	gate threshold voltage	$I_D = 10 mA; V_{GS} = V_{DS}$		2.0	2.6	4.0	V
					2.0		V
I_{DSS}	drain source leakage current	$V_{DS} = 1200 V; V_{GS} = 0 V$		1	100	μA	
I_{GSS}	gate source leakage current	$V_{DS} = 0 V; V_{GS} = 20 V$			250	nA	
R_G	internal gate resistance	$f = 1 MHz; V_{AC} = 25 mV, ESR \text{ of } C_{ISS}$		1.8		Ω	
C_{iss}	input capacitance	$V_{DS} = 1000 V; V_{GS} = 0 V; f = 1 MHz; T_{VJ} = 25^\circ C$		1895		pF	
C_{oss}	output capacitance			150		pF	
C_{rss}	reverse transfer (Miller) capacitance			10		pF	
Q_g	total gate charge	$V_{DS} = 800 V; I_D = 40 A; V_{GS} = -5/20 V; T_{VJ} = 25^\circ C$		115		nC	
Q_{gs}	gate source charge			28		nC	
Q_{gd}	gate drain (Miller) charge			37		nC	
$t_{d(on)}$	turn-on delay time	Inductive switching $T_{VJ} = 25^\circ C$ Free Wheeling Diode: Body Diode @ $V_{GS} = -5V$ $V_{DS} = 800 V; I_D = 40 A$ $V_{GS} = -5/20 V; R_G = 15 \Omega$ (external)		25.5		ns	
t_r	current rise time			11.1		ns	
$t_{d(off)}$	turn-off delay time			85		ns	
t_f	current fall time			23		ns	
E_{on}	turn-on energy per pulse			0.92		mJ	
E_{off}	turn-off energy per pulse			0.48		mJ	
$t_{d(on)}$	turn-on delay time	Inductive switching $T_{VJ} = 150^\circ C$ Free Wheeling Diode: Body Diode @ $V_{GS} = -5V$ $V_{DS} = 800 V; I_D = 40 A$ $V_{GS} = -5/20 V; R_G = 15 \Omega$ (external)		23.5		ns	
t_r	current rise time			9.8		ns	
$t_{d(off)}$	turn-off delay time			93		ns	
t_f	current fall time			25		ns	
E_{on}	turn-on energy per pulse			1.0		mJ	
E_{off}	turn-off energy per pulse			0.4		mJ	
R_{thJC}	thermal resistance junction to case				0.9	K/W	
R_{thJH}	thermal resistance junction to heatsink	with heatsink compound; IXYS test setup		1.15		K/W	

Source-Drain Diode				Ratings		
Symbol	Definitions	Conditions	min.	typ.	max.	
V_{SD}	forward voltage drop	$I_F = 20 A; V_{GS} = -5 V$			4.1	V
					3.5	V
t_{rr}	reverse recovery time	$V_{GS} = -5 V; I_F = 40 A$ $V_R = 800 V; -di_F/dt = 1000 A/\mu s$			55	ns
Q_{RM}	reverse recovery charge (intrinsic diode)				285	nC
I_{RM}	max. reverse recovery current				15	A

Note:

 When using SiC Body Diode the maximum recommended $V_{GS} = -5V$

Package SMPD			Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	
I_{RMS}	RMS current	wide terminal standard terminal			100 60	A A
T_{stg}	storage temperature		-55		150	°C
T_{op}	operation temperature		-55		150	°C
T_{vj}	virtual junction temperature		-55		175	°C
Weight				8		g
F_c	mounting force with clip		40		130	N
$d_{Spp/App}$	creepage distance on surface /	terminal to terminal	1.6			mm
$d_{Spb/Apb}$	striking distance through air	terminal to backside	4.0			mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute		3000 2500		V V
		50/60 Hz; RMS; $I_{ISOL} < 1 \text{ mA}$				



Digits

1 to 19: Part #

20 to 23: Date Code

24 to 25: Assembly line

26 to 31: Lot #

32: Split Lot

33 to 36: Individual #

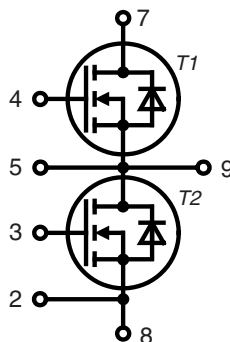
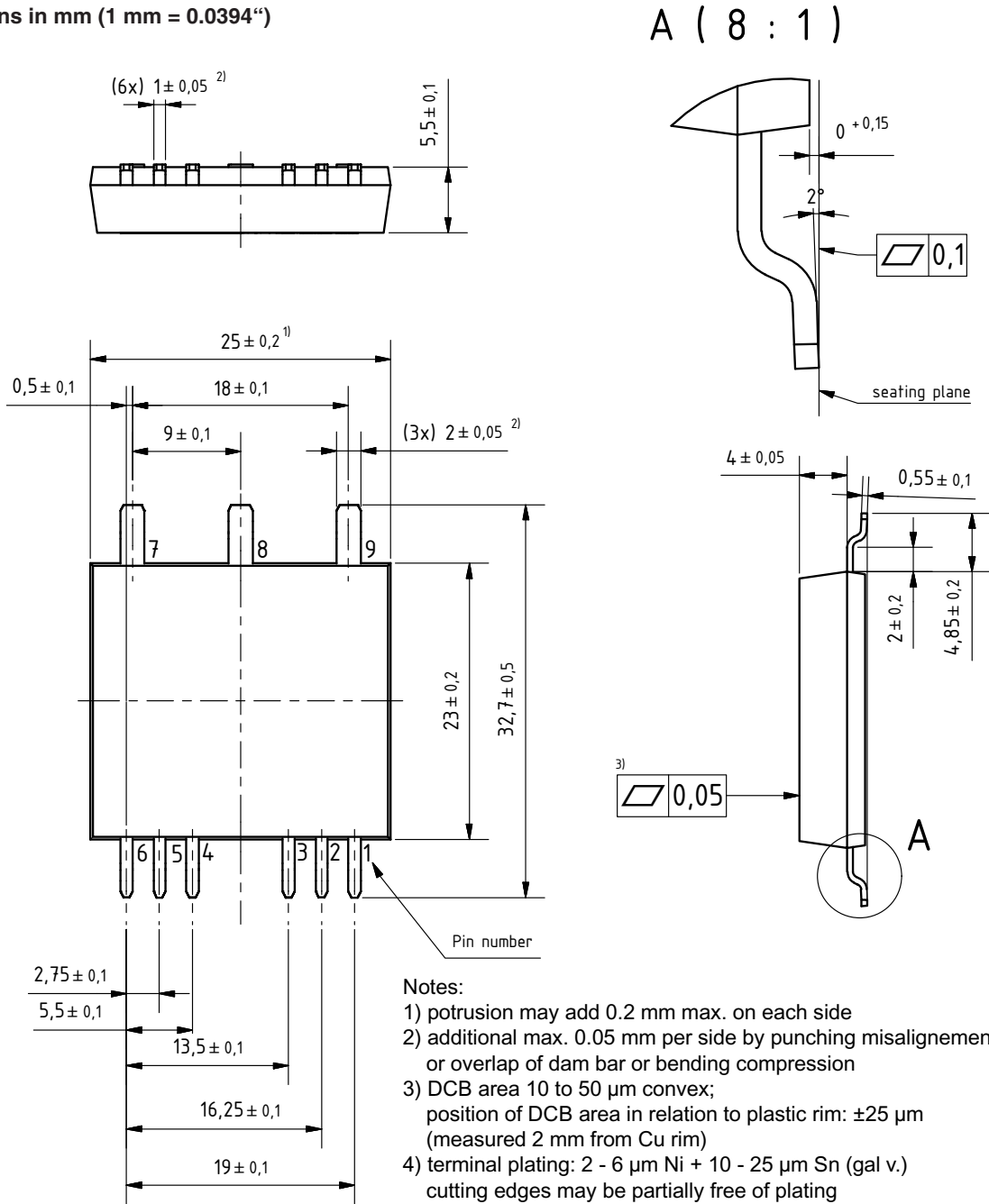
Part number

M = Mosfet
 C = SiC MOSFET
 B = Generation 2
 30 = Current Rating [A]
 P = Phase leg
 1200 = Reverse Voltage [V]
 LB = SMPD-B

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MCB30P1200LB-TUB	MCB30P1200LB	Tube	20	MCB30P1200LB-TUB
Alternative	MCB30P1200LB-TRR	MCB30P1200LB	Tape&Reel	200	MCB30P1200LB-TRR

Outlines SMPD-B

Dimensions in mm (1 mm = 0.0394")



Curves

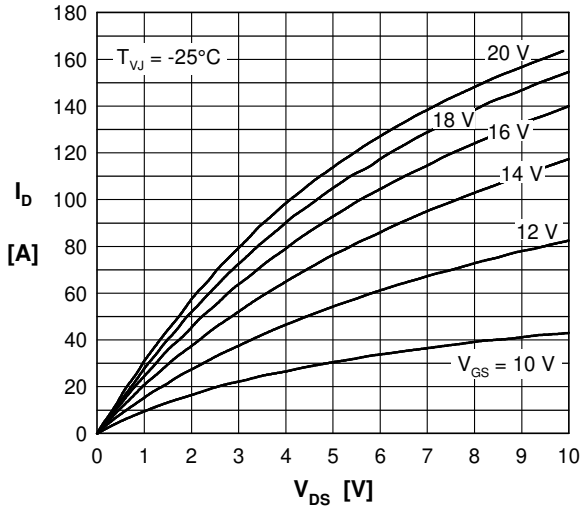


Fig. 1 Typical output characteristics (-25°C)

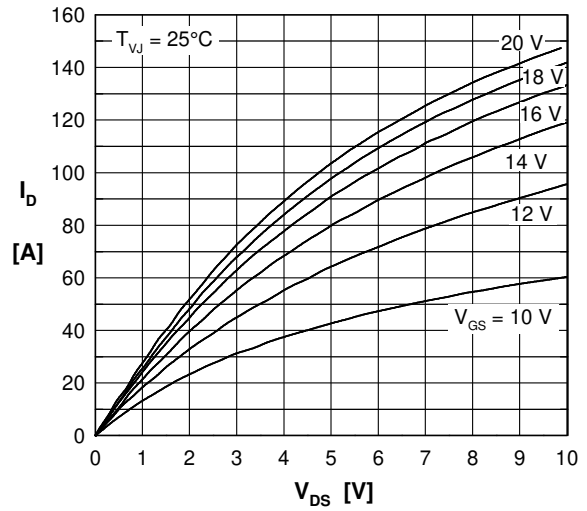


Fig. 2 Typical output characteristics (25°C)

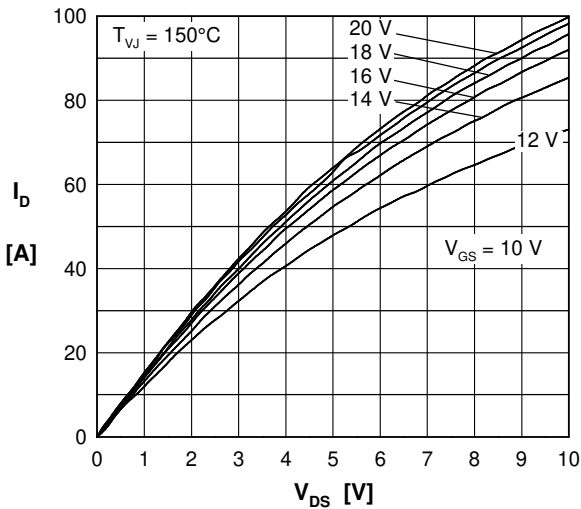


Fig. 3 Typical output characteristics (150°C)

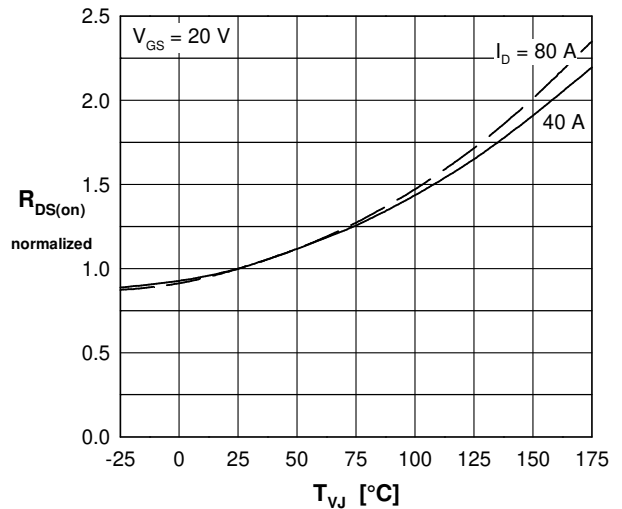


Fig. 4 $R_{DS(on)}$ normalized vs. junction temperature T_{VJ}

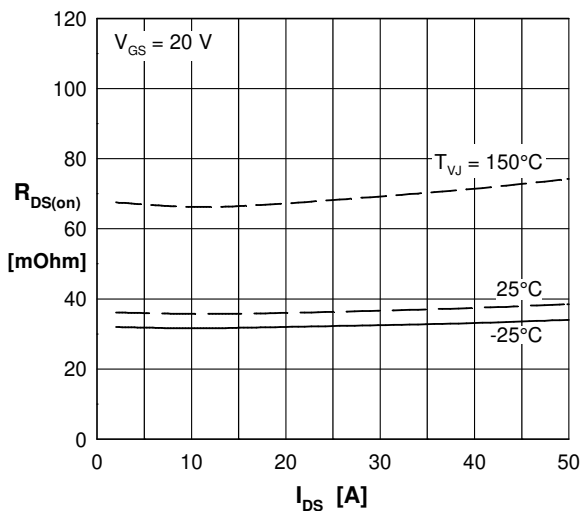


Fig. 5 $R_{DS(on)}$ versus drain current

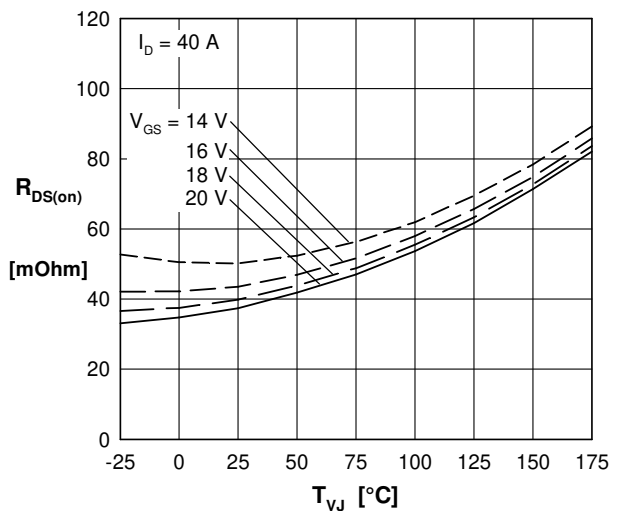


Fig. 6 $R_{DS(on)}$ versus junction temperature T_{VJ}

Curves

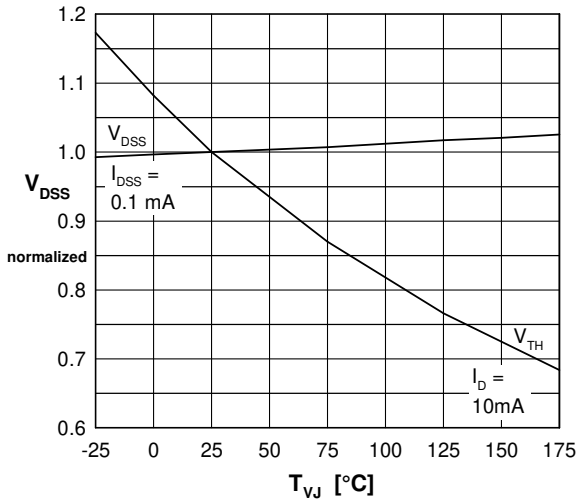


Fig. 7 Norm. breakdown V_{DSS} & threshold voltage V_{TH} versus junction temperature T_{VJ}

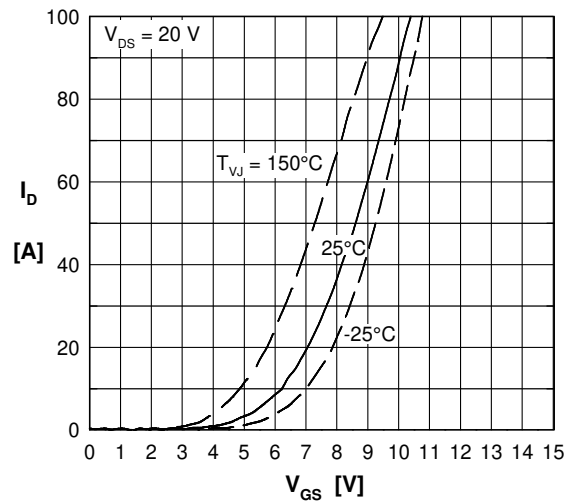


Fig. 8 Typical transfer characteristics

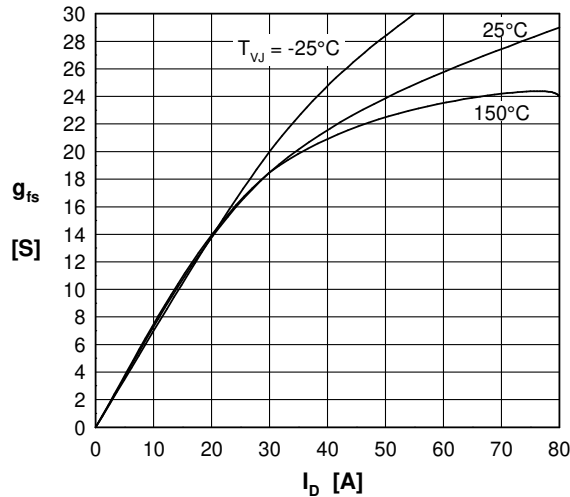


Fig. 9 Typical forward transconductance

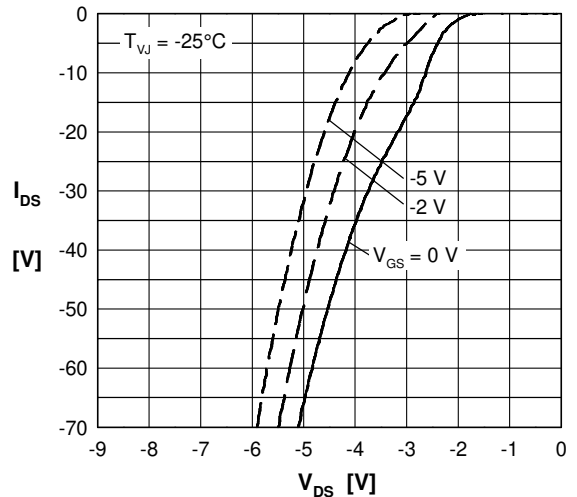


Fig. 10 Forward voltage drop of intrinsic diode versus V_{DS} measured at -55°C

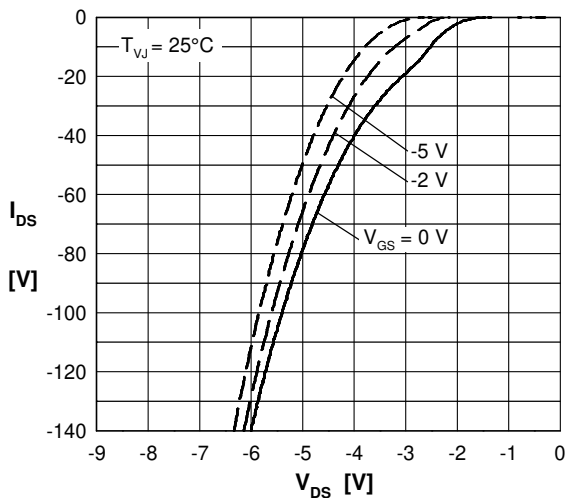


Fig. 11 Forward voltage drop of intrinsic diode versus V_{DS} measured at 25°C

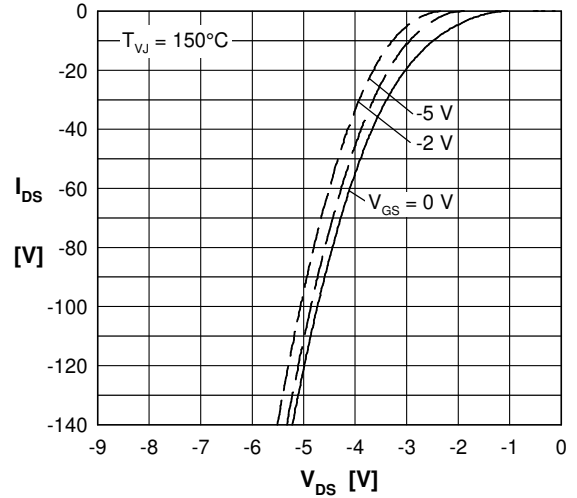


Fig. 12 Forward voltage drop of intrinsic diode versus V_{DS} measured at 150°C

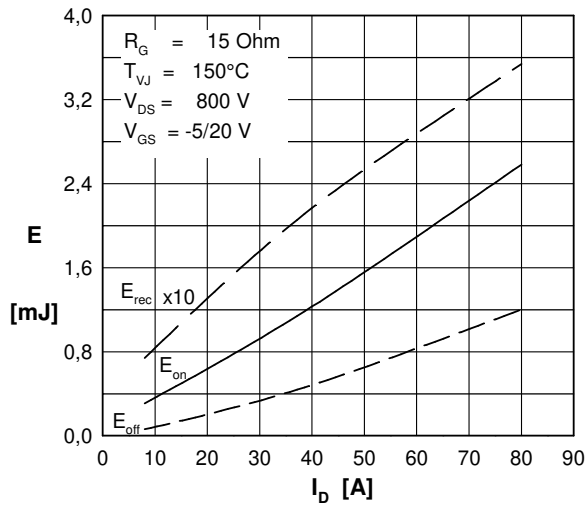
Curves


Fig. 13 Typical switching energy versus drain current

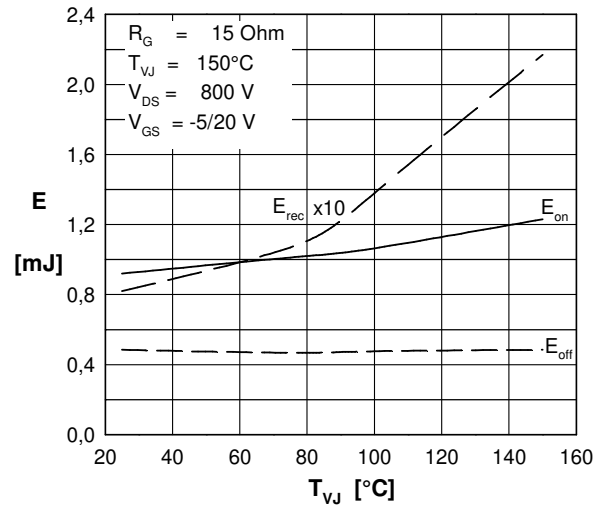


Fig. 14 Typical switching energy versus temperature

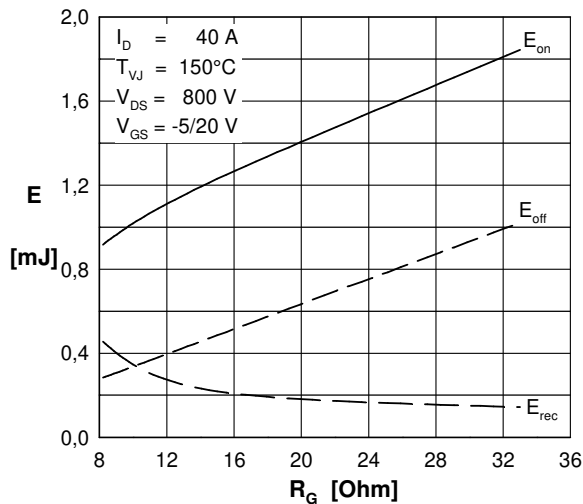


Fig. 15 Typical switching energy versus external gate resistor

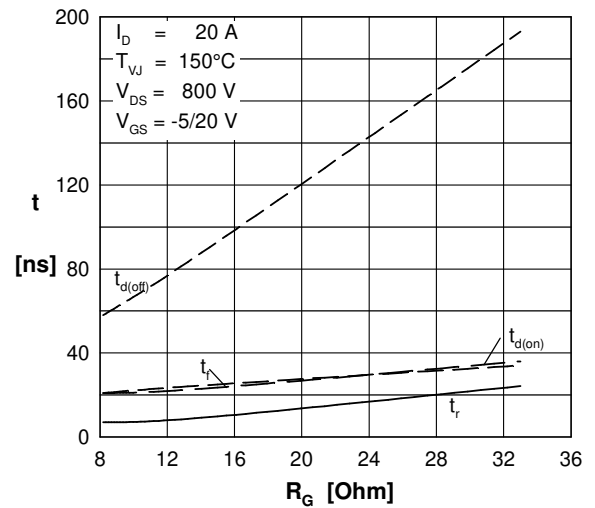


Fig. 16 Typical switching time versus external gate resistor

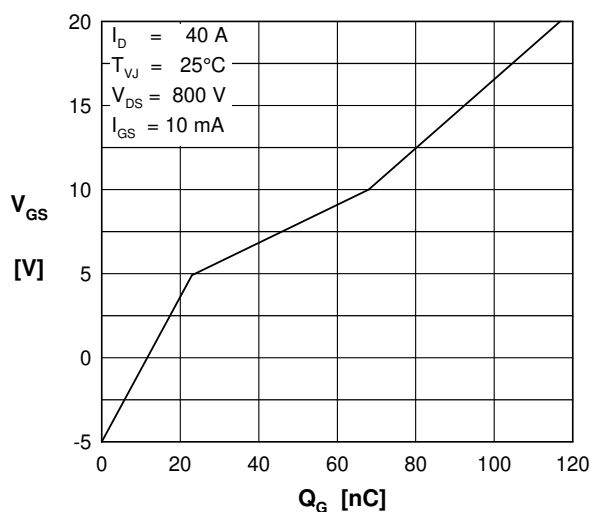


Fig. 17 Typical turn on gate charge, trendline

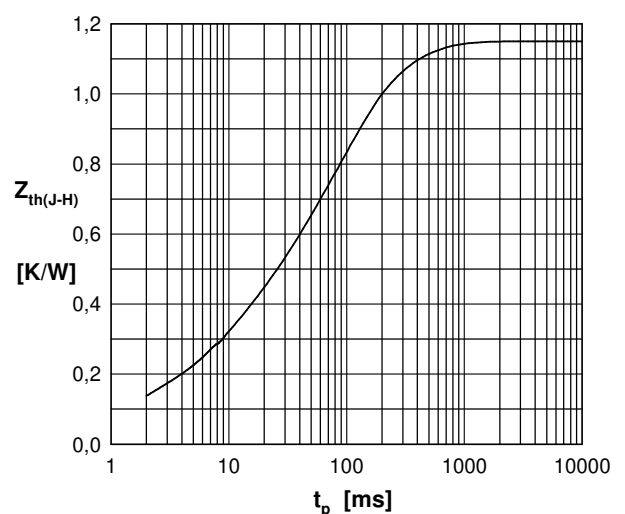


Fig. 18 Typical transient thermal impedance